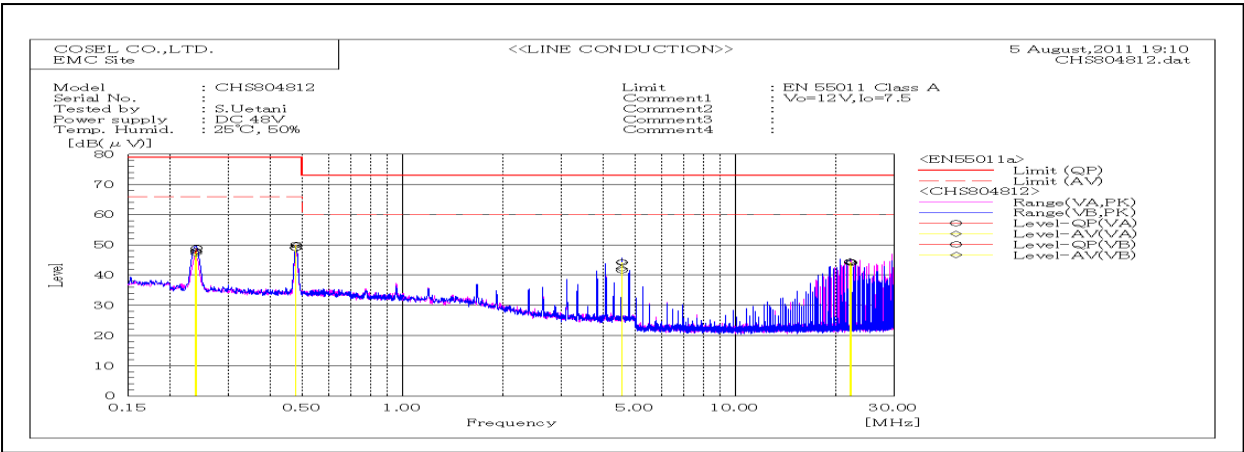
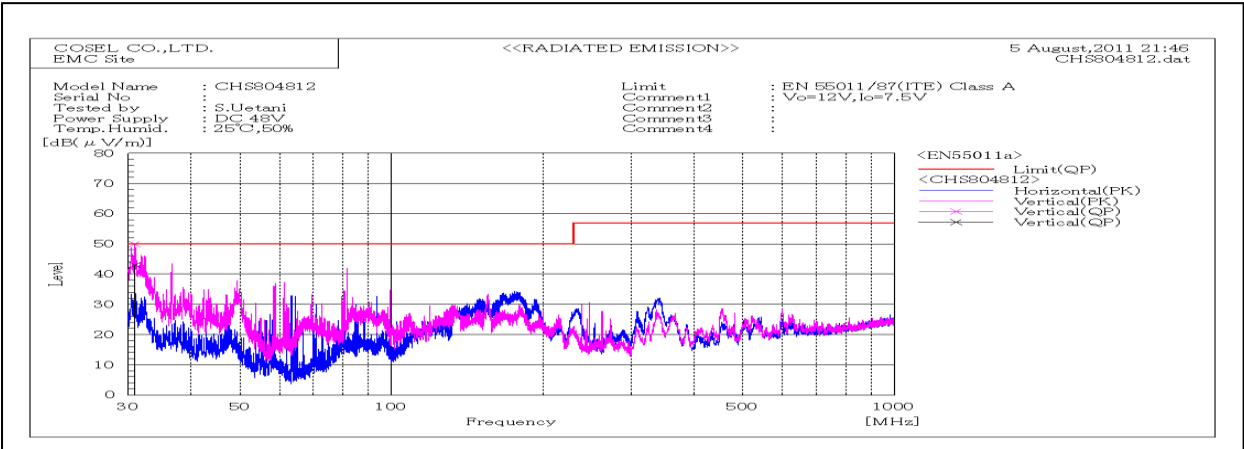


DATA SHEET		Date	27-Apr-21
Model	CHS804812	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	S.Uetani



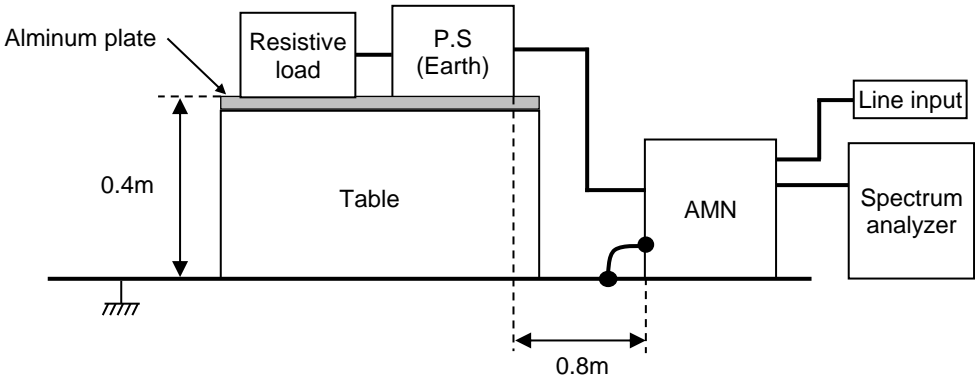
Frequency MHz	Harm	Line Phase	Reading dB(μV)		Factor dB	Level dB(μV)		Limit dB(μV)		Margin dB		Pass/ Fail	Remark
			QP	AV		QP	AV	QP	AV	QP	AV		
0.23934		VB	37.9	37	10.1	48	47.1	79	66	31	18.9	Pass	
0.24067		VA	38.8	37.7	10.1	48.9	47.8	79	66	30.1	18.2	Pass	
0.47797		VA	39	38.7	10.1	49.1	48.8	79	66	29.9	17.2	Pass	
0.47873		VB	39.9	39.8	10.1	50	49.9	79	66	29	16.1	Pass	
4.55446		VB	33.9	34.1	10.3	44.2	44.4	73	60	28.8	15.6	Pass	
4.55473		VA	31.3	31.9	10.3	41.6	42.2	73	60	31.4	17.8	Pass	
22.0546		VB	33.5	33.6	10.9	44.4	44.5	73	60	28.6	15.5	Pass	
22.2935		VA	33.1	33.2	11	44.1	44.2	73	60	28.9	15.8	Pass	



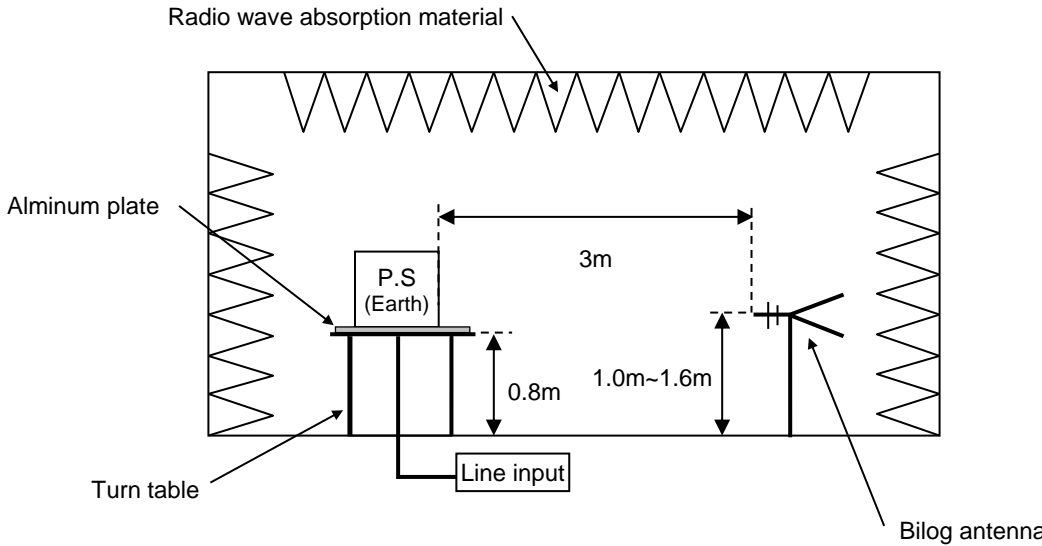
Frequency MHz	Harm	Polariz ation	Stabili ty	Reading dB(μV)		Space Loss dB	Level dB(mW)		Limit dB(mW)	Margin dB	Pass/ Fail	Height cm	Angle deg	Remark
				QP	AV		QP	AV						
30.92		V	Stable	56.9	-13.9		43	50		7	Pass	101	353	

DATA SHEET		Date	27-Apr-21
Model	Circuit used for measurement	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	S.Uetani

1. Line conduction



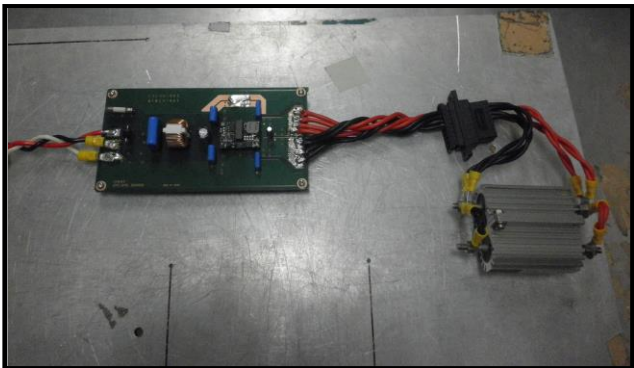
2. Radiated emission



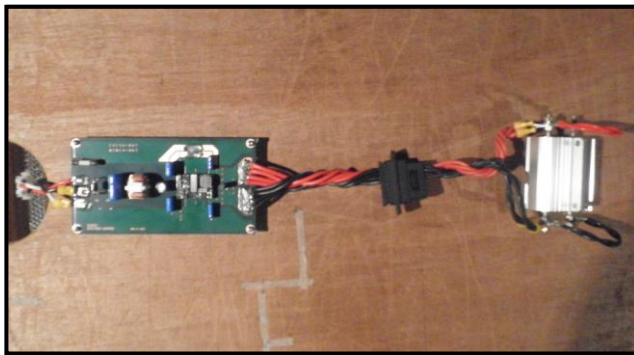
TEST :EMI
Model Name :CHS804812

Date 2011/10/4

○Photographs of Test Set-Up
LINE CONDUCTION



RADIATED EMISSION



○ Testing circuitry

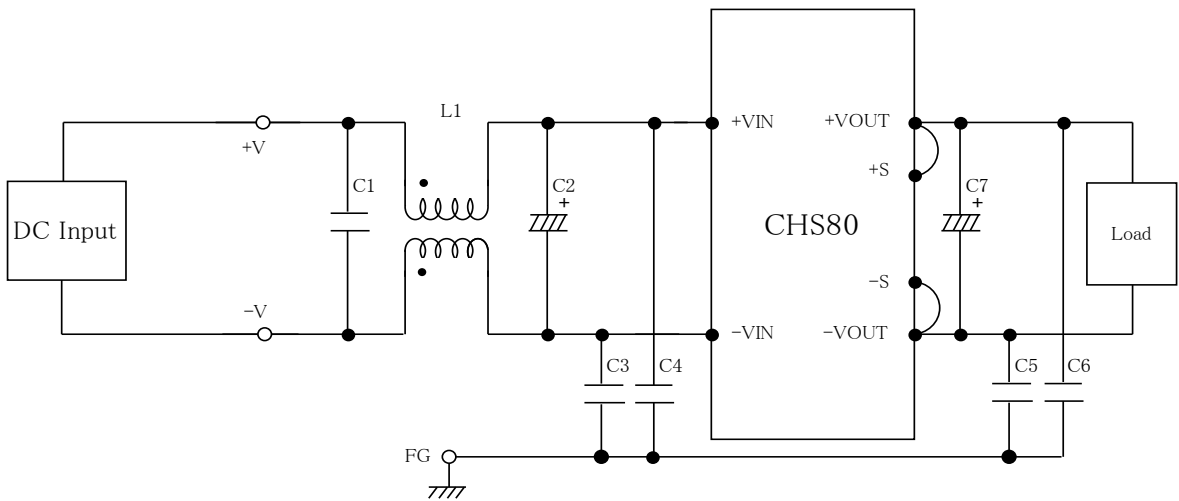


Fig.1 Testing circuitry

- L1 : 1mH SC-05-10J (TOKIN)
- C1 : 250V 2.2 μ F FPD22E225J4 (NITSUKO)
- C2 : 100V 33 μ F PWseries (nichicon)
- C3,C4 : 630V 0.068 μ F FPD22J683J4 (NITSUKO)
- C5,C6 : 630V 0.033 μ F FPD22J333J4 (NITSUKO)
- C7 : 50V 10 μ F PMseries (nichicon)